

BUK7208-40B

N-channel TrenchMOS standard level FET Rev. 03 — 7 June 2010

Product data sheet

Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 185 °C rating

1.3 Applications

- 12 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 185 °C		-	-	40	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	<u>[1]</u>	-	-	75	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2		-	-	167	W
Static chara	acteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{\text{see } \frac{\text{Figure 12}}{\text{Figure 12}};$		-	6.6	8	mΩ
Avalanche	ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 75 \text{ A; } V_{\text{sup}} \leq 40 \text{ V;} \\ R_{\text{GS}} &= 50 \Omega; V_{\text{GS}} = 10 \text{ V;} \\ T_{j(\text{init})} &= 25 ^{\circ}\text{C; } \text{ unclamped} \end{split}$		-	-	242	mJ
Dynamic ch	Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V; } I_D = 25 \text{ A;}$ $V_{DS} = 32 \text{ V; } T_j = 25 \text{ °C;}$ see Figure 13		-	11.5	-	nC

^[1] Continuous current is limited by package.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain[1]	mb	D
3	S	source		_G (EA)
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT428 (DPAK)	

^[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package	Package					
	Name	Description	Version				
BUK7208-40B	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428				

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

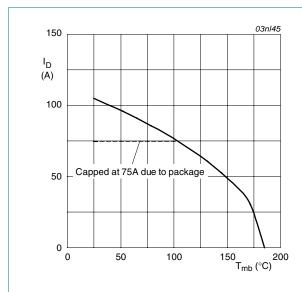
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 185 °C		-	-	40	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	40	V
V_{GS}	gate-source voltage			-20	-	20	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> ;	[1]	-	-	105	Α
		see Figure 3	[2]	-	-	75	Α
		$T_{mb} = 100 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{}$	[2]	-	-	75	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; $t_p \le 10 \mu s$; pulsed; see <u>Figure 3</u>		-	-	420	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	167	W
T_{stg}	storage temperature			-55	-	185	°C
Tj	junction temperature			-55	-	185	°C
Source-drain	n diode						
I _S	source current	T _{mb} = 25 °C	[2]	-	-	75	Α
			[1]	-	-	105	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	-	420	Α
Avalanche ru	uggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 75 A; $V_{sup} \le 40$ V; R_{GS} = 50 Ω ; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	242	mJ

^[1] Current is limited by power dissipation chip rating.

^[2] Continuous current is limited by package.

03no96

150 T_{mb} (°C) 200



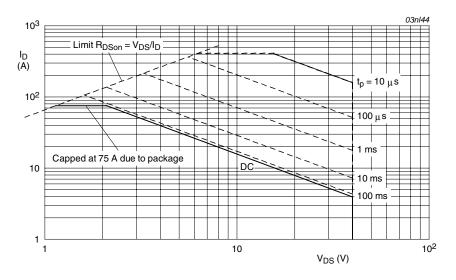


120 P_{der} (%) 80 40 0 50

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 1. Normalized continuous drain current as a function of mounting base temperature

Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25^{\circ}C; I_{DM}$ is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.95	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		-	71.4	-	K/W

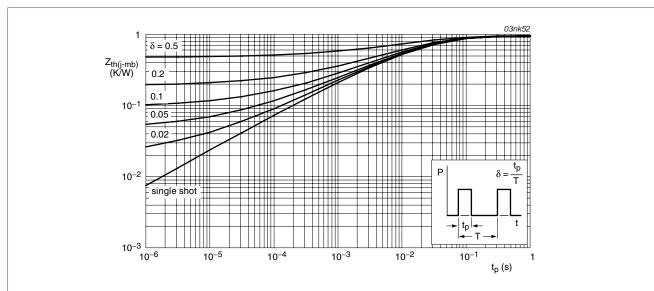


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS} drain-source breakd voltage	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	40	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see Figure 10	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 10	-	-	4.4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 185$ °C; see <u>Figure 10</u>	0.9	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 185 ^{\circ}\text{C}$	-	-	500	μΑ
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
I _{GSS}	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
DOON	drain-source on-state resistance	$V_{GS} = 10 \text{ V}$; $I_D = 25 \text{ A}$; $T_j = 185 \text{ °C}$; see Figure 11; see Figure 12	-	-	15.6	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 11; see Figure 12	-	6.6	8	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{}$	-	35	-	nC
Q _{GS}	gate-source charge		-	9.8	-	nC
Q_{GD}	gate-drain charge		-	11.5	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V; } V_{DS} = 25 \text{ V; } f = 1 \text{ MHz;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 14}}{\text{Figure 14}}$	-	1870	2493	pF
C _{oss}	output capacitance		-	482	578	pF
C _{rss}	reverse transfer capacitance		-	201	275	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	16	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega$; $T_j = 25 °C$	-	104	-	ns
t _{d(off)}	turn-off delay time		-	47	-	ns
t _f	fall time		-	51	-	ns
L _D	internal drain inductance	measured from drain to centre of die ; $T_j = 25 ^{\circ}\text{C}$	-	2.5	-	nΗ
L _S	internal source inductance	measured form source lead to source bond pad ; T _j = 25 °C	-	7.5	-	nΗ
Source-d	rain diode					
V_{SD}	source-drain voltage	$I_S = 17 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see Figure 15	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	50	-	ns
Qr	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	36	-	nC

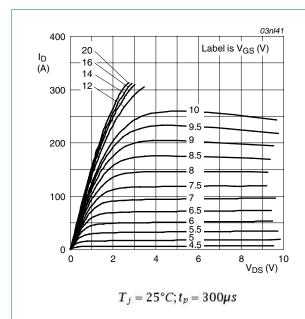


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

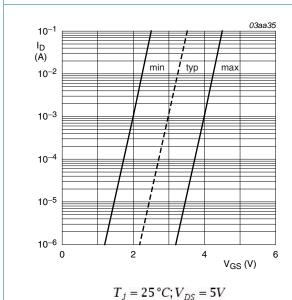


Fig 7. Sub-threshold drain current as a function of gate-source voltage

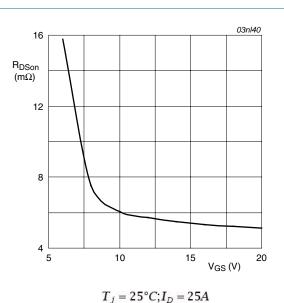


Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

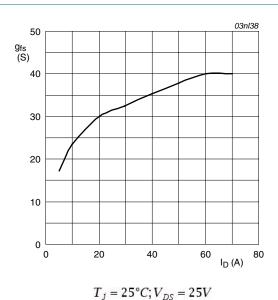


Fig 8. Forward transconductance as a function of drain current; typical values

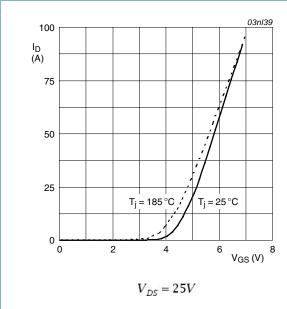


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

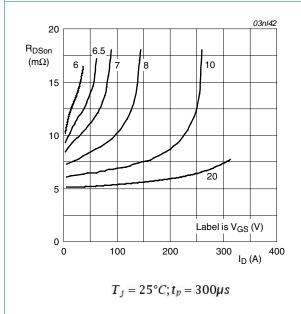
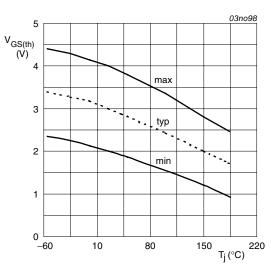


Fig 11. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 1mA; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature

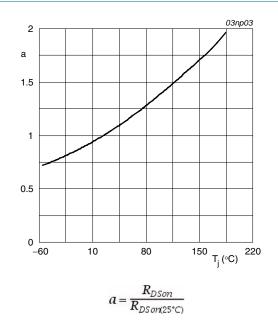


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

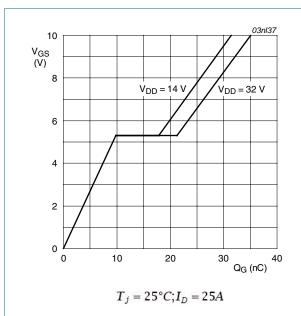
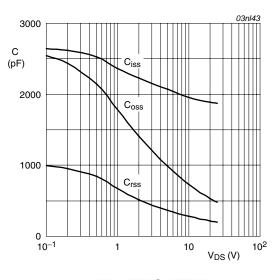


Fig 13. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

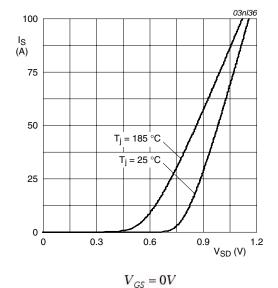


Fig 15. Source current as a function of source-drain voltage; typical values

7. Package outline

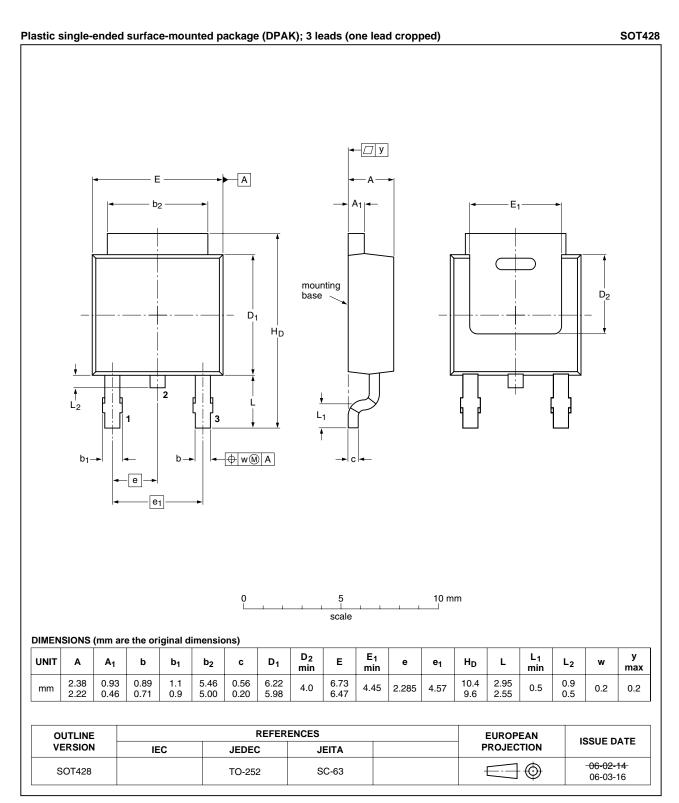


Fig 16. Package outline SOT428 (DPAK)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BUK7208-40B_3	20100607	Product data sheet	-	BUK7208-40B_2		
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 					
 Legal texts have been adapted to the new company name where appropriate. 						
BUK7208-40B_2	20040122	Product data	-	BUK7208-40B_1		
BUK7208-40B_1	20021212	Objective data	-	-		

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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